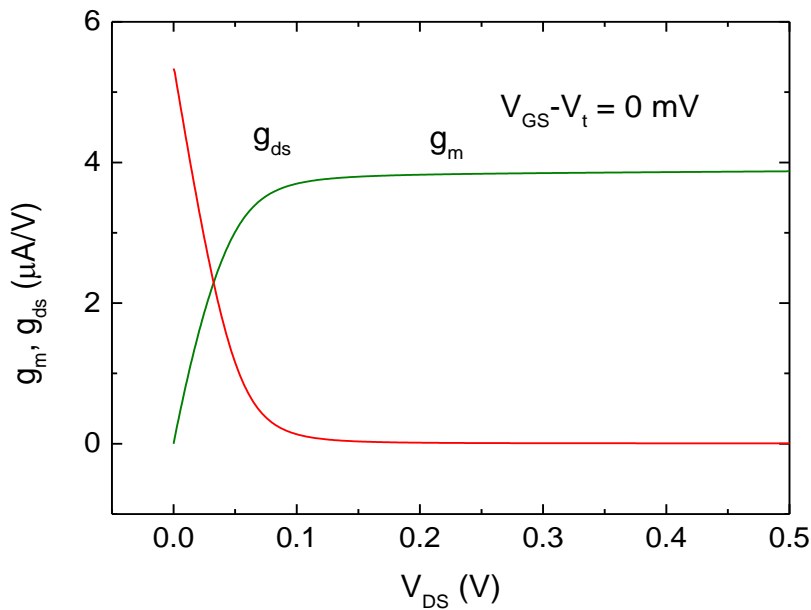
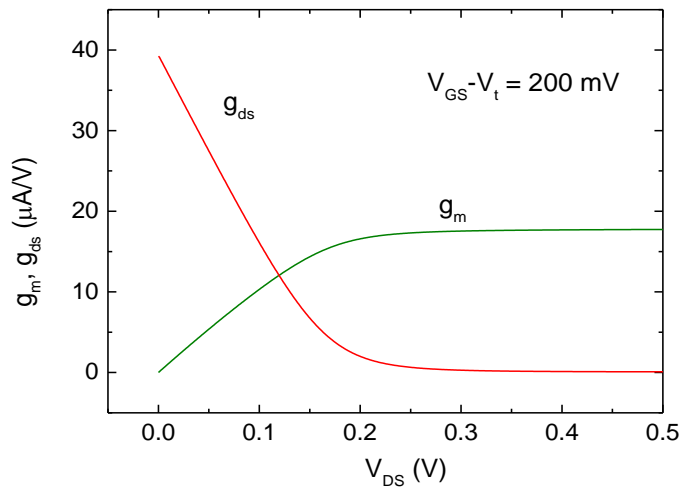
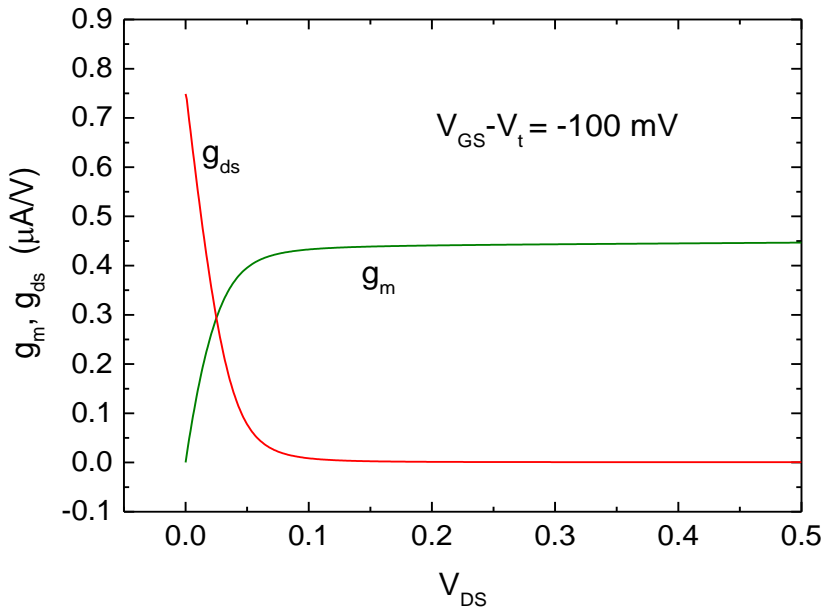


Example of simulated dc characteristics

1. n-MOS, 0.25 μm CMOS process. $W=10 \mu\text{m}$, $L=10 \mu\text{m}$. Simulator: LTSpice

gm and gds as a function of VDS for different overdrive voltages





I_D and V_{TE} as a function of $V_{GS} - V_t$

